

## INCHANGE SEMICONDUCTOR

# isc N-Channel MOSFET Transistor

# FCH067N65S3

### • FEATURES

- With TO-247 packaging
- High speed switching
- · Very high commutation ruggedness
- · Easy to use
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

#### APPLICATIONS

- PFC stages
- Power supply
- Switching applications

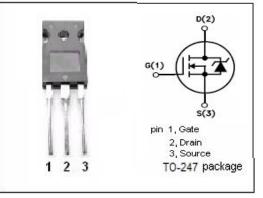
SYMBOL	PARAMETER	VALUE	UNIT	
V <sub>DSS</sub>	Drain-Source Voltage	650	V	
V <sub>GSS</sub>	Gate-Source Voltage	±30	V	
ID	$\begin{array}{l} \text{Drain Current-Continuous} @T_{\text{C}} = 25^{\circ} \text{C} \\ T_{\text{C}} = 100^{\circ} \text{C} \end{array}$	44 28	А	
I <sub>DM</sub>	Drain Current-Single Pulsed	110	А	
PD	Total Dissipation	312	W	
Tj	Operating Junction Temperature	-55~150	°C	
T <sub>stg</sub>	Storage Temperature	-55~150	°C	

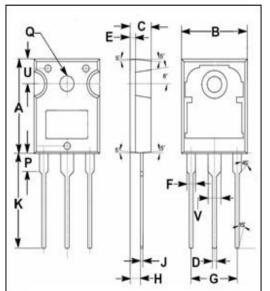
### • ABSOLUTE MAXIMUM RATINGS(T<sub>a</sub>=25<sup>°</sup>C)

#### THERMAL CHARACTERISTICS

SYMBOL	PARAMETER		UNIT	
Rth(ch-c)	Channel-to-case thermal resistance	0.4	°C <b>/W</b>	
Rth(ch-a)	Channel-to-ambient thermal resistance	40	°C/W	

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	mm	
DIM	MIN	MAX
Α	19.80	20.20
В	15.40	15.80
С	4.90	5.10
D	0.90	1.10
Ε	1.40	1.60
F	1.90	2.10
G	10.80	11.00
Н	2.40	2.60
J	0.50	0.70
K	19.50	20.50
Ρ	3.90	4.10
Q	3.30	3.50
U	5.20	5.40
V	2.90	3.10

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### **ELECTRICAL CHARACTERISTICS**

#### $T_{C}\text{=}25^{\circ}\!\!\!\mathrm{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	ТҮР	МАХ	UNIT
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V; I <sub>D</sub> = 1mA	650			V
V <sub>GS</sub> (th)	Gate Threshold Voltage	V <sub>DS</sub> =V <sub>GS</sub> ; I <sub>D</sub> =4.4mA	2.5		4.5	V
R <sub>DS(on)</sub>	Drain-Source On-Resistance	V <sub>GS</sub> = 10V; I <sub>D</sub> =22A		59	67	mΩ
I <sub>GSS</sub>	Gate-Source Leakage Current	V <sub>GS</sub> = ±30V;V <sub>DS</sub> =0V			±0.1	μA
I <sub>DSS</sub>	Drain-Source Leakage Current	V <sub>DS</sub> = 500V; V <sub>GS</sub> = 0V;Tc=25°C V <sub>DS</sub> = 500V; V <sub>GS</sub> = 0V;Tc=125°C			1 100	μA
V <sub>SDF</sub>	Diode forward voltage	I <sub>SD</sub> =22A, V <sub>GS</sub> = 0 V			1.2	V

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